

AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A compound semiconductor substrate for epitaxial growth, wherein when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of a substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm,

the haze is not more than 2 ppm all over an effectively used area of the substrate and an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein the effectively used area includes the surface area of the substrate, with the exception of the peripheral part including the chamfered part of the substrate.

2. **(Original)** The compound semiconductor substrate as claimed in claim 1, wherein the haze is not more than 1 ppm all over the effectively used area of the substrate.

3. **(Original)** The compound semiconductor substrate as claimed in claim 1 or 2, wherein the compound semiconductor substrate is an InP substrate.

4. **(Original)** The compound semiconductor substrate as claimed in claim 3, wherein a dislocation density is not more than 1000/cm².

5. **(Original)** The compound semiconductor substrate as claimed in claim 4, wherein the dislocation density is not more than 500/cm².